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Claims

1. A photosensitive element comprising a support film which comprises a biaxially oriented polyester film and a

5 photosensitive resin composition layer formed on one surface of the polyester film,

wherein a resin layer containing fine particles is formed on the opposite surface of the support film to which the photosensitive resin composition layer is formed, and said photosensitive resin composition comprises

- (A) a binder polymer having a carboxyl group,
- (B) a photopolymerizable compound having at least one polymerizable ethylenically unsaturated group in the molecule, and
- 15 (C) a photopolymerization initiator.
 - 2. A photosensitive element having a layer of a photosensitive resin composition on a support film, which comprises having a heat shrinkage ratio in the lateral direction of the support film at 200°C for 30 minutes being 0.00 to 4.00%, and said photosensitive resin composition comprises
 - (A) a binder polymer having a carboxyl group,
 - (B) a photopolymerizable compound having at least one polymerizable ethylenically unsaturated group in the molecule,
- 25 and

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- (C) a photopolymerization initiator.
- The photosensitive element according to Claim 2, wherein the heat shrinkage ratio in the lateral direction of the support
 film at 150°C for 30 minutes is 0.00 to 0.20%.
 - 4. The photosensitive element according to Claim 2, wherein the heat shrinkage ratio in the lateral direction of the support film at 105°C for 30 minutes is 0.00 to 0.20%.
 - 5. A photosensitive element having a layer of a photosensitive

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resin composition on a support film, which comprises having a heat shrinkage ratio in the lateral direction of the support film at 150°C for 30 minutes being 0.00 to 0.20%, and said photosensitive resin composition comprises

- 5 (A) a binder polymer having a carboxyl group,
 - (B) a photopolymerizable compound having at least one polymerizable ethylenically unsaturated group in the molecule, and
 - (C) a photopolymerization initiator.

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- 6. The photosensitive element according to Claim 5, wherein the heat shrinkage ratio in the lateral direction of the support film at 105°C for 30 minutes is 0.00 to 0.20%.
- 7. A photosensitive element having a layer of a photosensitive resin composition on a support film, wherein a contact angle (°) of the support film with water satisfies the following numerical formula (1):

(Contact angle at X surface) / (Contact

20 angle at Y surface) > 1.1

(1)

wherein X surface means a surface of the support film to which the photosensitive resin composition is coated and dried; and Y surface means a surface of the support film opposite to the surface to which the photosensitive resin composition is coated,

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and said photosensitive resin composition comprises

- (A) a binder polymer having a carboxyl group,
- (B) a photopolymerizable compound having at least one polymerizable ethylenically unsaturated group in the molecule,

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- (C) a photopolymerization initiator.
- 8. The above photosensitive element according to Claim 2, wherein the support film is a support film comprising a resin layer containing fine particles being laminated on one surface of a biaxially oriented polyester film, and the photosensitive

resin composition layer is coated and dried on the opposite surface of the support film to which the resin layer is formed.

- 9. The photosensitive element according to Claim 1, wherein an average particle size of the fine particles is 0.01 to 5.0 μm .
- 10. The photosensitive element according to Claim 1, wherein a thickness of the resin layer containing fine particles is 0.05 to 5.0 µm.
 - 11. The photosensitive element according to Claim 1, wherein a haze of the support film is 0.01 to 5.0%.
- 15 12. The photosensitive element according to Claim 1, wherein a heat shrinkage ratio in the longitudinal direction of the support film at 105°C for 30 minutes is 0.30 to 0.60%.
- 13. The photosensitive element according to Claim 1, wherein 20 a heat shrinkage ratio in the longitudinal direction of the support film at 150°C for 30 minutes is 1.00 to 1.90%.
- 14. The photosensitive element according to Claim 1, wherein a heat shrinkage ratio in the longitudinal direction of the support film at 200°C for 30 minutes is 3.00 to 6.50%.
 - 15. The photosensitive element according to Claim 1, wherein a weight average molecular weight of (A) the binder polymer having a carboxyl group is 20,000 to 300,000.
 - 16. The photosensitive element according to Claim 1, wherein an acid value of (A) the binder polymer having a carboxyl group is 50 to 300 mg KOH/g.
- 35 17. The photosensitive element according to Claim 1, wherein (B) the photopolymerizable compound is a bisphenol A type

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(meth)acrylate compound.

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- 18. The photosensitive element according to Claim 1, wherein (C) the photopolymerization initiator is 2,4,5-triaryl imidazole dimer.
- 19. The photosensitive element according to Claim 1, wherein formulation amounts of Components (A), (B) and (C) are 40 to 80 parts by weight of Component (A) based on 100 parts by weight of Component (A) and Component (B) in total, 20 to 60 parts by weight of Component (B) based on 100 parts by weight of Component (A) and Component (B) in total, and 0.01 to 20 parts by weight of Component (C) based on 100 parts by weight of Component (A) and Component (B) in total.
- 20. A photosensitive element roll according to any one of Claims 1 to 19, wherein the above photosensitive element is wound up or rolled around a core.
- 21. A photosensitive element roll in which the photosensitive element is wound up around a core, wherein a total height of winding deviation at the edge surface of the photosensitive element roll after naturally dropping the photosensitive element roll five times from the height of 10 cm to the collision surface so that the axis direction of the core becomes perpendicular to the collision surface is 1 mm or less.
- 22. A process for preparing a resist pattern which comprises laminating the photosensitive element according to any one of Claims 1 to 20 to a substrate for forming a circuit so that the photosensitive resin composition layer is closely contacted to the substrate, irradiating imagewisely active light to photocure the exposed portion, and removing an unexposed portion by development.
 - 23. A resist pattern prepared by the preparation process

according to Claim 22.

- 24. A resist pattern in which unevenness on the side surface of the resist pattern is 0 to 3.0 μm .
- 25. A resist pattern in which a number of unevenness larger than 3.0 μ m on the center line of the side surface of the resist pattern is 0 to 5/4 mm.
- 10 26. A resist pattern in which a mathematical average roughness (Ra) on the side surface of the resist pattern is 0 to 2.0 µm.
 - 27. The resist pattern according to Claim 26, wherein a maximum height ($R_{\rm y}$) on the side surface of the resist pattern is 0 to 3.0 μm .
 - 28. A resist pattern comprising a maximum height (R $_{\!Y})$ on the side surface of the resist pattern of 0 to 3.0 $\mu m\,.$
 - 29. The resist pattern according to any one of Claims 24 to 28, wherein a width of the resist pattern is 1 μm or more.
 - 30. The resist pattern according to any one of Claims 24 to 28, wherein a height of the resist pattern is 1 to 150 µm.
 - 31. The resist pattern laminated substrate which comprises the resist pattern according to any one of Claims 24 to 28, wherein it is formed on a substrate for preparing a circuit.
- 30 32. A process for preparing a wiring pattern which comprises subjecting the resist pattern laminated substrate according to Claim 31 to etching or plating.
- 33. A wiring pattern prepared by the process for preparing the35 wiring pattern according to Claim 32.

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- 34. A wiring pattern in which unevenness on the side surface of the wiring pattern is 0 to 3.0 $\mu m\,.$
- 35. A wiring pattern in which a number of unevenness larger than 3.0 μm on the center line of the side surface of the wiring pattern is 0 to 5/4 mm.
 - 36. A wiring pattern in which a mathematical average roughness (R_a) on the side surface of the wiring pattern is 0 to 2.0 μm .
- 37. The wiring pattern according to Claim 36, wherein a maximum height ($R_{
 m y}$) on the side surface of the wiring pattern is 0 to
- 15 38. A wiring pattern comprising a maximum height (R_y) on the side surface of the wiring pattern of 0 to 3.0 μm .
 - 39. The wiring pattern according to any one of Claims 34 to 38, wherein a width of the wiring pattern is 1 μm or more.
 - 40. The wiring pattern according to any one of Claims 34 to
 - 38, wherein a height of the wiring pattern is 0.01 to 200 µm.

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3.0 µm.